

# Guard-Ring-Free InGaAs/InP Single-Photon Avalanche Diode Based on a Novel One-Step Zn-diffusion Technique

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**Abstract**—This work presents a novel InGaAs/InP SPAD structure fabricated using a selective area growth (SAG) method. The surface topography of the selectively grown film deposited within the 70  $\mu\text{m}$  diffusion apertures is used to engineer the Zn diffusion profile to suppress premature edge breakdown. The device achieves a highly uniform active area without the need for shallow diffused guard ring (GR) regions that are inherent in standard InGaAs/InP SPADs. We have obtained 33% and 43% photon detection probability (PDP) at 1550 nm, with 5 V and 7 V excess bias, respectively. These measurements were performed at 300K and 225K. The dark count rate (DCR) per unit area at room temperature and at 5 V excess bias is 430 cps/ $\mu\text{m}^2$  and it decreases to 5 cps/ $\mu\text{m}^2$  at 225K. Timing jitter is measured with passive quenching at 1550 nm as 149 ps at full-width-at-half-maximum (FWHM), (300K, 5 V excess bias). The proposed technology is suitable for a number of applications, including optical time-domain reflectometry (OTDR), quantum information, and light detection and ranging (LiDAR).

**Index Terms**—InGaAs/InP, LiDAR, Photon counting, Single-photon avalanche diodes (SPADs), Three-dimensional (3-D) ranging, Time-correlated single-photon counting (TCSPC), III-V

## I. INTRODUCTION

LOW-LEVEL-LIGHT detection in short-wave-infrared (SWIR) wavelengths with high spatial and timing accuracy is a growing area of interest by the virtue of applications such as quantum information [1], OTDR [2], and LiDAR [3]–[6]. Various device structures have been proposed to target these applications. Superconducting nanowire single-photon detectors have shown remarkable detection efficiency and timing jitter performance, but they require cryogenic temperature

operation which limits their application areas [7]–[9]. Ge-on-Si single-photon avalanche diodes (SPADs) have the potential of being integrated within a single chip together with CMOS read-out electronics, but the lattice mismatch between Si and Ge has been a significant challenge delaying the acceptance of such detectors. Recently significant improvement has been shown in the performance of Ge-on-Si SPADs [10], but compared to InGaAs/InP SPADs, they show higher noise and lower operating temperature. Thus, InGaAs/InP SPADs are still the default technology for the applications in SWIR.

This work aims to develop a SPAD pixel that operates at SWIR region to be used in a LiDAR camera. Operating at SWIR wavelengths for LiDAR applications has various advantages such as lower attenuation due to atmosphere, and reduced background noise from black-body radiation of the Sun. Moreover, eye safety limits are higher at SWIR wavelengths [3]. Compared to visible wavelengths, 1550 nm benefits from significantly higher permissible input power. As a result, it is possible to detect objects at a higher distance. In addition to operation wavelength, pixel performance metrics like timing jitter, photon detection probability, noise, and pixel pitch play a crucial role for LiDAR. Therefore, in the proposed structure, low noise pixels with highly uniform PDP throughout the active pixel area are targeted, along with good timing resolution.

There have been significant efforts to improve the performance of InGaAs/InP SPADs through optimizing the Zn diffusion profile, layer dopings and thicknesses [11]–[14]. However, all these designs are based on a standard double diffusion guard ring in which a significant part of the pixel area is not active. Moreover, this type of device usually exhibits enhanced electric field at the device periphery at low excess biases. Some groups have worked on one-step diffusion-based InGaAs/InP SPADs by applying recess-etching [15], [16]. However, their performance is quite low compared to double-diffusion-based ones. In this work, a novel InGaAs/InP SPAD structure based on SAG is proposed [17]. Edge breakdown is prevented by a single diffusion thanks to the surface topography of SAG epitaxy. Device has a very uniform electric field even at low excess bias. In addition, as the extra area of the GR region is preserved, this approach has the potential of achieving a smaller pixel pitch for the same active area. Thus, it enables larger pixel arrays to reach a better spatial resolution. The

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SAG topography is also highly reproducible, and does not require frequent tuning. Besides, compared to the double Zn-diffusion technique, the SAG process offers an advantage in the reduced complexity of the diffusion depth calibration, since only one diffusion run needs to be taken into account. Hence, SAG method based InGaAs/InP SPAD technology is a very promising candidate to develop next-generation LiDAR applications.

## II. DEVICE DESIGN

### A. Device Structure

Device design utilizes lattice-matched  $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$  (hereafter referred to as InGaAs) ternary semiconductor material for photon absorption and InP for avalanche multiplication. The device structure is demonstrated in Fig. 1. This kind of layer structure is referred to as separate absorption, grading, charge, and multiplication (SAGCM) type. It is designed to confine the high electric field required for avalanche multiplication, inside the large bandgap (1.34 eV) InP region, while a modest electric field is formed in the absorber InGaAs region to sweep photogenerated carriers from InGaAs to InP. This is achieved by inserting a narrow n-type doped InP charge sheet. The electric field difference between the absorption and multiplication regions is strictly determined by the doping concentration and the thickness of the charge sheet. A five-step grading layer is grown between charge and absorber layers to ensure a smooth transition in the valance band [18]. The final structure has  $\sim 1.8 \mu\text{m}$  thick i-InGaAs absorber, and  $\sim 3 \mu\text{m}$  thick i-InP cap layers where  $2 \mu\text{m}$  Zn diffusion was performed.  $1.8 \mu\text{m}$  thick i-InGaAs layer allows to absorb almost all the incident light which passes through the absorber two times thanks to the back-side metallization.  $1 \mu\text{m}$  thick multiplication width was selected to keep the tunneling contribution in DCR low whilst not degrading the jitter of the device [19]. Then, the i-InP cap layer was made thick enough for Zn diffusion, and a low field enhancement effect at the device edge is thus obtained by avoiding excessively sharp junction curvature.  $\sim 0.1 \mu\text{m}$  thick n-InP charge layer was doped in the range of  $2\text{-}2.5 \times 10^{17} \text{ cm}^{-3}$  to have  $25 \text{ V} \pm 5 \text{ V}$  difference between the punch-through and breakdown point, which ensures the complete depletion of the absorber. After the epitaxial growth and Zn diffusion process, the back-side of the device is fully covered with Au metal to form the cathode contact. A ring-shaped, ohmic metallization of  $5 \mu\text{m}$  width, and  $56 \mu\text{m}$  inner diameter is then deposited around the periphery of the device for the anode metallization. The active area of the device is therefore partially shaded by the ohmic metal. This design was adopted for ease of testing with front-side illumination; however, for eventual smaller diameter devices or pixelated arrays, a backside-illuminated geometry would be advantageous in order to maximize the anode electrical contact area without causing optical shading.

In standard InGaAs/InP SPADs, a double diffusion technique is used to prevent premature edge breakdown. A deep Zn diffusion defines the active area while a shallow diffusion on the periphery of the device prevents a steep variation of the depletion front. This approach has been proven to

be a successful method by many groups for suppressing edge breakdown. However, the area covered by the shallow diffusion increases the device size while it does not contribute to the efficiency of the device. As a result, the fill factor of the device becomes sub-optimal. In the proposed design, edge breakdown is successfully prevented by a single diffusion step thanks to SAG. Prior to Zn diffusion, a  $\sim 300 \text{ nm}$  thick undoped InP layer was grown by SAG at the center of the device. The thickness of this layer gradually rises from center to mask edge due to enhanced growth rate [20], and it reaches  $\sim 700 \text{ nm}$  at the device edge. Zn diffuses through the tapered InP surface such that the doping profile inside InP has a steady transition towards the periphery. This ensures that the electric field around the device edge is lower than the center. The diameter of the diffusion window for this particular device is  $70 \mu\text{m}$ . Further details on the device fabrication are explained in [17]. To be able to test the operability of the same process conditions in Geiger mode, and perform detailed active area scanning analysis in a more effective way, in this study, large-diameter devices were selected. The most significant variation in the SAG topography and resulting Zn diffusion depth profile occurs over a length scale of  $< \sim 5 \mu\text{m}$ , thus we can reasonably expect that the process will be applicable to device diameters in the range of  $10\text{-}15 \mu\text{m}$ . Demonstration of small device diameters and state-of-the-art pixel pitches thanks to the SAG method is an ongoing future work.

### B. Device Simulations

The electrical simulations of the device are performed using Synopsys TCAD commercial software. Doping values measured with the SIMS method given in [21] were used for Zn diffusion, charge, and grading regions. As for the lateral doping profile, the Zn diffusion edge curvature of the simulated device was adjusted to match approximately the curvature seen on the SEM images of the device cross-section from [17]. Regarding the avalanche generation, the quasi-physical model from [22] is first used to calculate the impact ionization coefficients in InP. In the TCAD environment, the Okuto-Crowell model [23] was utilized for the avalanche process, where fitting parameters are adjusted to match ionization coefficients between [22] and TCAD under various electric fields. The simulated breakdown voltages based on this model have presented a good agreement with measured ones from various devices. In Fig. 3 the difference of about  $0.5 \text{ V}$

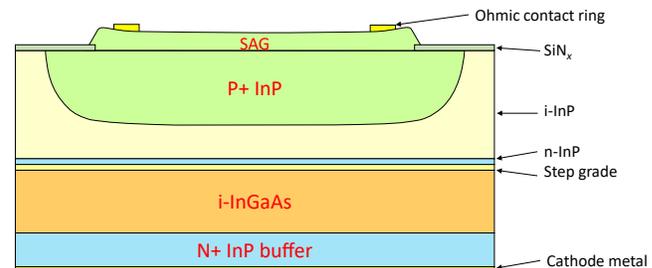


Fig. 1. Schematic of SAG based InGaAs/InP SPAD. Green parts highlight the InP doped by Zn.

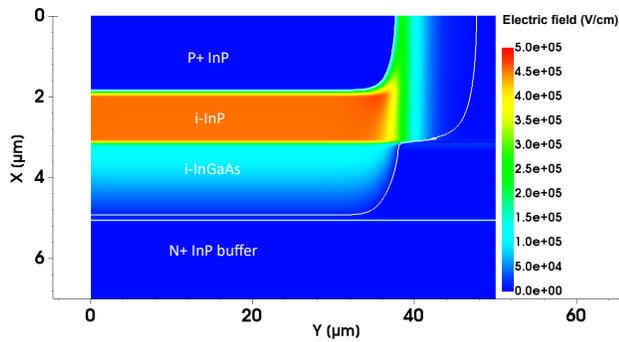


Fig. 2. 2D electric-field simulation of half device at 300K and at 5 V excess bias.

between the measured and simulated breakdown voltage arises most probably from a variation in the doping of the charge region. The doping in this region has a strong influence on the breakdown voltage and a variation of only a few percent in this level can cause a noticeable difference in the breakdown voltage. Moreover, a slight difference between simulated and actual multiplication width may also have a contribution in this difference. In order to obtain the I-V curve below breakdown voltage, typical lifetime values for InGaAs [24] and InP [25] materials were plugged in from literature, which are at the order of  $\mu\text{s}$ . Then, the surface current was defined between cap i-InP and SiN layers by introducing traps at the interface. Trap locations were assumed to be at the mid-gap position. Trap concentration and cross section were used as fitting parameters to have good matching with experimental I-V.

The electric field distribution of the device at 5 V excess bias and at 300K is depicted in Fig. 2. It shows that the high electric field is well confined below the diffused region. Moreover, the engineered diffusion front at the periphery is successful in eliminating the edge breakdown. Also, the electric field inside the absorber region has a linear gradient due to n-type background doping. It is kept below 150 kV/cm which is sufficiently low to prevent tunneling noise, and it reaches to 15 kV/cm at the InP buffer interface, which ensures that the absorber is fully depleted [18].

### III. MEASUREMENT RESULTS

Geiger-mode characterizations were performed in gated mode to suppress afterpulsing at high excess bias voltages. A DC voltage that is 1 V lower than the breakdown voltage of the SPAD was summed with a square pulse of 50 ns duration by utilizing a commercial bias-tee. The summed voltage was applied to the cathode of the device and the output pulse was read from the anode through a 50 k $\Omega$  resistor to passively quench the SPAD. The number of pulses are counted by a digital oscilloscope (Teledyne LeCroy WavePro 760Zi-A) connected to the quenching resistor. Temperature sweeps are done by employing a compact liquid nitrogen cooler stage (Linkham LTS420E-P).

#### A. I-V Characteristics

The I-V curves (acquired by Agilent SMU B2902A at room temperature) under illumination and dark conditions are depicted in Fig. 3. A 1550 nm laser is used to illuminate the devices and identify the punch-through voltage. Since this wavelength is not absorbed by the InP layer, the voltage at which photocurrent develops indicates that the InGaAs absorber region is depleted. The device shows a sharp avalanche breakdown at 65 V and a punch trough voltage of  $\sim 43$  V which ensures the absorber region will be depleted for a broad temperature range.

#### B. Active Area Scan

In order to investigate the uniformity of the electric field within the device, a 1550 nm laser beam is focused on the device through a confocal microscope. The focused light beam was shifted in a window of 120  $\mu\text{m}$  x 120  $\mu\text{m}$  with a step size of 1  $\mu\text{m}$  and at each beam position, the count rate of the SPAD was recorded. Photomaps are regarded as the examination of the electric field within the device since the regions with a photoresponse are the regions where avalanche multiplication occurs. In addition to the device shown in Fig. 1, another device with two floating GRs was also measured to investigate their impact on device performance. Its cross-section is shown in Fig. 5. Fig. 4 demonstrates the measured 2D photomap of the device without GR at 3, 5, and 7 V excess biases and Fig. 5 shows it for the device with two floating GRs at 3 and 5 V excess biases. A highly uniform response is observed at 3 V excess bias while at 5 and 7 V excess biases anomalous side lobes appear for the device without a GR. The maximum sidelobe to center response ratio at 3 and 5 V excess biases are 55 % and 70% respectively. However, the photoresponse of the device with floating GRs is dominated by the side lobes at 3 V excess bias. At 5 V excess bias, the field at the sidelobe saturates, as a result the peak responses at the center and the sidelobes become similar. In agreement with the photocurrent maps reported here [17], sidelobes occur along [100] and [010] crystal directions. The uniformity of the SAG surface around the mask edge was disturbed along these directions which resulted in a deeper Zn diffusion and enhanced electric field.

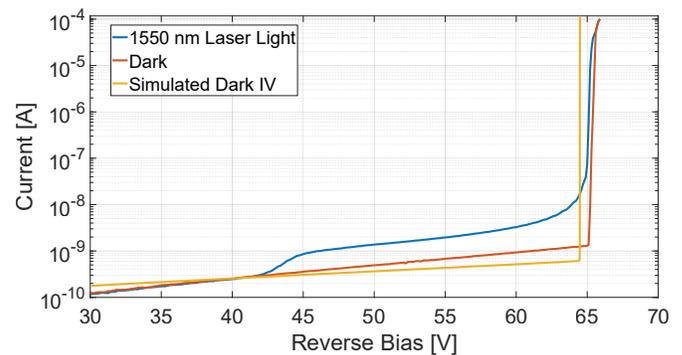


Fig. 3. I-V measurements of SAG-based InGaAs/InP SPAD in dark and under 1550 nm wavelength light illumination together with simulated I-V curve at 300K.

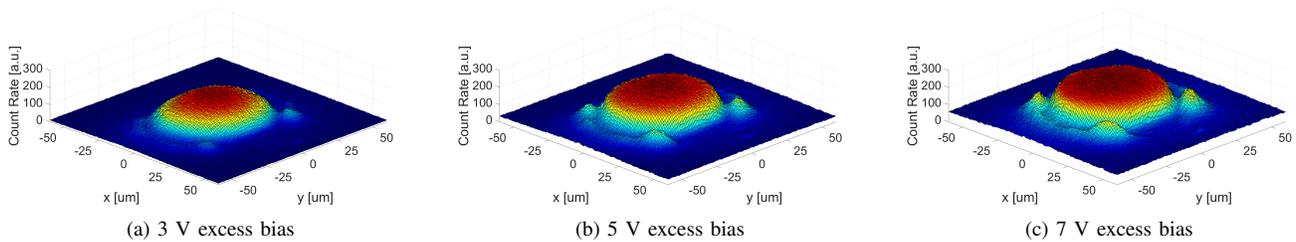


Fig. 4. Active area scans of the device without GR under focused 1550 nm laser light at 300K.

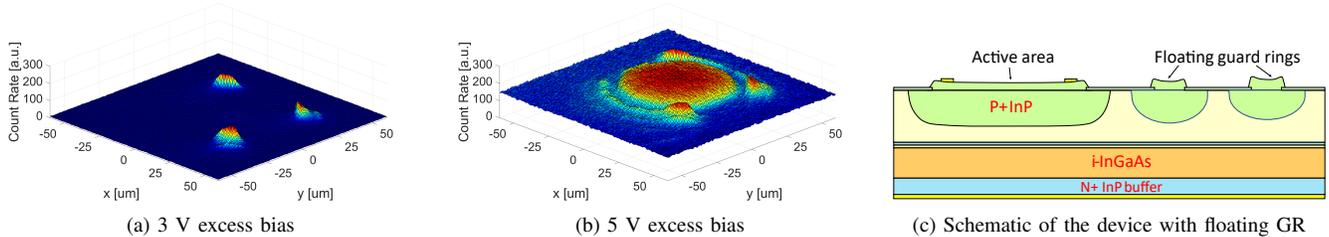


Fig. 5. Active area scans of the device with two floating GRs under focused 1550 nm laser light at 300K. The scan could not be performed at 7 V excess bias due to high DCR that is probably arising from the high electric field on the sidelobes. While there are also floating guard rings on the left side of the device, they are not shown in the schematic.

The SAG process achieves edge effect suppression by relying on the growth enhancement at the edge of the device, which is driven by near-surface diffusion of the growth precursors over the masked areas of the wafer [26]. In the floating GR devices, this growth enhancement is most pronounced in the outermost open areas, which are the floating GRs, with less growth enhancement at the edge of the active area compared to non-floating GR devices. This may be the reason for less effective suppression of edge enhancement for the floating GR devices, which in this case manifests itself in the anomalous lobe features observed along specific directions at the edge of the device. Finally, the effective active area is calculated for the scan results in Fig. 4 by integrating the regions which have a response higher than the half maximum. Calculated diameters based on the effective active area are 53  $\mu\text{m}$ , 59  $\mu\text{m}$ , and 63  $\mu\text{m}$  at 3, 5, and 7 V excess biases respectively. Partial shading induced by the anode metallization is visible as a blue region in Fig. 5b between the center active region and sidelobes.

### C. Noise Performance

The noise floor of a SPAD determines the minimum distinguishable photon rate incident on the device. Pulses that appear in the absence of light presence establish the noise of a SPAD. Primary dark pulses appear due to intrinsic carrier generation in bulk semiconductor, and secondary dark pulses occur as trapped charges from a previously triggered avalanche escape the trap confinement potential over a longer time constant. The former is referred to as primary DCR while the latter is called afterpulsing. The main generation mechanisms that contribute to DCR are Shockley-Read-Hall (SRH) from InGaAs and trap-assisted tunneling (TAT) from InP. SRH is highly correlated to crystal quality and TAT generation can be enhanced in regions

of high electric field. Afterpulsing is a dominant process for InGaAs/InP SPADs and it is usually controlled by limiting the amount of charge flowing during avalanche current generation and keeping the SPAD below breakdown voltage until all the trapped carriers are released.

1) *DCR*: Measurements of primary DCR are realized at a gate-off time of 250  $\mu\text{s}$  to neglect afterpulsing. Results with respect to excess bias for a temperature range of 225K-300K are plotted in Fig. 6 and Fig. 7. The device without GR demonstrates a DCR of 20 kcps at 225K and 5 V excess bias. At room temperature, DCR reaches up to 1.6 Mcps due to thermal generation in the absorber region.

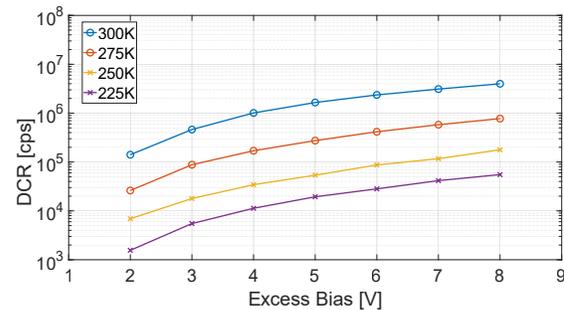


Fig. 6. DCR measurement of the device without GR from 225K-300K and 2 V-8 V.

The device with GR has shown DCRs that are about one order of magnitude higher than guard ringless device at all temperatures. A more clear DCR comparison of the two devices can be found in Fig. 8. As highlighted, at 3 V excess bias while only small sidelobes are active for the device with floating GRs, its DCR reaches the level of the one without GR. In other words, the DCR contribution of the small sidelobes is

comparable to the DCR arising from the entire active area of the device without GR. At 5 V excess bias, when the center regions of both devices are active, the DCR ratio of the two devices becomes  $\sim 4$  which indicates that a significant part of the DCR of the device with GR results from the enhanced electric field at the sidelobes. This is further investigated by activation energy curves. Under the assumption that SRH generation is the dominant primary DCR source, the relation between DCR and temperature can be described as

$$DCR \propto T^2 \cdot e^{\frac{-E_a}{kT}}, \quad (1)$$

where  $E_a$  is the activation energy and  $k$  is Boltzmann's constant [27]. Activation energies at 5 and 7 V excess biases are obtained by plotting  $\ln(DCR/T^2)$  vs.  $1/kT$  and fitting a linear curve as in Fig. 9. An activation energy of 0.37 eV is measured at 5 V excess bias for the device without GR. This energy level corresponds to the half bandgap of InGaAs and indicates dominant DCR mechanism down to 230K is SRH generation in the absorber region. On the other hand, the activation energy for the device with GR is 0.34 eV ( $< 0.37$  eV) at 5 V excess bias. That indicates the DCR is not solely dominated by the SRH mechanism but instead is a combination of SRH and TAT. Activation energies decrease also at 7 V excess bias due to enhanced electric field for both devices.

It should be noted that sidelobes reach a response level that is comparable to the center of the device without GR at 7 V excess bias. DCR generated at these sidelobes is degrading the device performance. Thus, there is some room to improve the DCR of the device without GR by optimizing the SAG process to eliminate sidelobes.

2) *Afterpulsing*: Ruling out the contribution of afterpulsing to primary DCR and PDP is an important aspect for accurate characterization of the device performance. Afterpulsing could result in overestimation of DCR and PDP as it can cause higher count rates. A reliable method to ensure afterpulsing is fully eliminated is to use a long enough gate-off time such that all traps are released. Fig. 10 shows the DCR vs. gate-off time at temperatures from 225K to 300K. At all temperatures, there is an increase in DCR for the gate-off times shorter than 20  $\mu$ s. The increase is sharper for lower temperatures due to enhanced

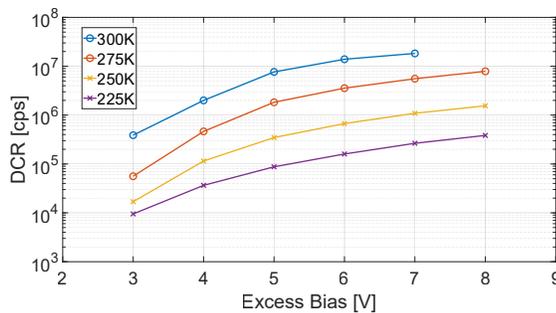


Fig. 7. DCR measurement of the device with two floating GRs from 225K-300K and 3 V-8 V. Due to count rate saturation at 8 V excess bias at 300K, the result is not plotted at this particular point.

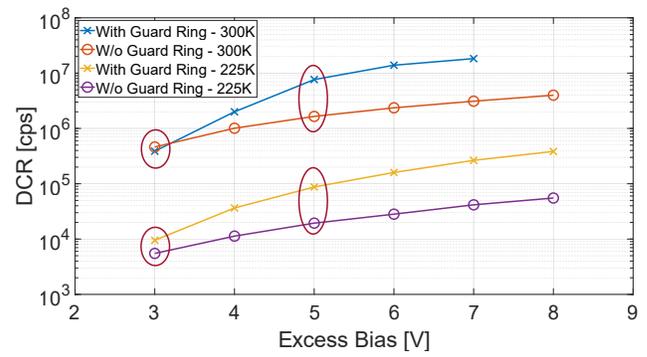


Fig. 8. DCR results of both devices at 225K and 300K. Values at 3 V and 5 V excess bias are highlighted.

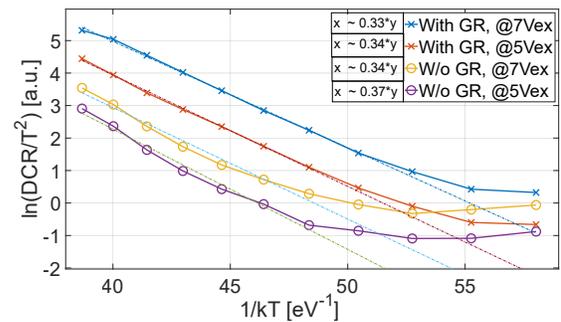


Fig. 9. Activation energy curves of both devices at 5 V and 7 V excess biases.

trap lifetimes. The point of increase in DCR strongly depends on the number of trapped carriers which is proportional to the charge that is flowing during an avalanche. Moreover, the amount of charge is affected by pulse duration. Therefore, a shorter gate-on time would result in a shift in the curve towards a shorter gate-off duration. At long gate-off times, DCR does not vary, meaning afterpulsing does not impact the count rate. Therefore, 250  $\mu$ s gate-off time at 50 ns is used for PDP measurement similar to primary DCR measurements.

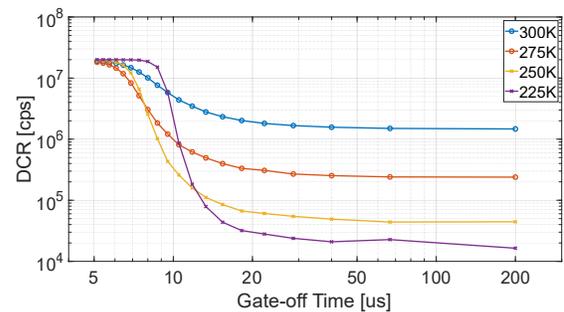


Fig. 10. DCR vs. Gate-off time for the device without GR at 50 ns gate-on time and at 5 V excess bias.

#### D. Photon Detection Probability

PDP measurements were performed based on the setup shown in Fig. 11. A laser pulse of length  $\sim 40$  ps at 1550 nm wavelength is utilized. Laser pulse and electrical gate are synchronized by the waveform generator such that photons

reach the SPAD while its voltage is above breakdown. Light power is divided through a beam splitter such that high output end is connected to a power meter to calculate the number of photons incident on the device. Power at the low output end is attenuated further and focused on the SPAD by the confocal microscope. The main advantage of a PDP measurement with a focused beam is that ambiguity on the active area is avoided. When PDP is measured by illuminating the entire chip area, inaccuracies in estimating the active device area could impact the result significantly [13]. Moreover, charge persistence could cause uncertainty in the active area especially at low temperatures [12], [28], [29]. PDP is calculated by the equation

$$PDP = \frac{1}{\mu} \cdot \ln \left[ \frac{1 - C_d/f}{1 - C_t/f} \right], \quad (2)$$

where  $C_d$  stands for the number of dark counts per second,  $C_t$  for the total number of counts per second under illumination,  $f$  is the gate frequency, and  $\mu$  is the average number of photons per optical pulse [27]. A PDP of 32% was measured at an excess bias of 5 V, while at 7 V, it grew to 43%. Measured PDP values do not vary significantly at 225K and 300K consistently with literature [27]. PDP rises as excess bias increases due to the enhanced electric field in the avalanche region and higher breakdown probability. However, PDP saturates as impact ionization coefficients saturate at high excess bias [30].

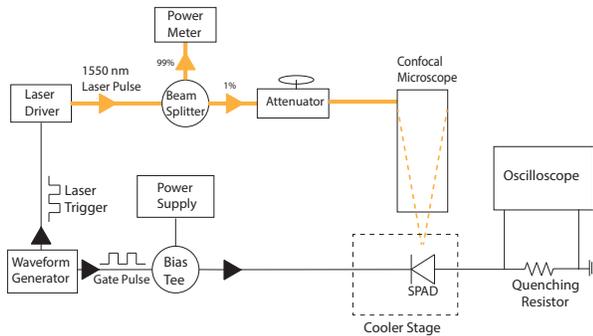


Fig. 11. Schematic of PDP measurement setup. Black lines show electrical connections while yellow ones correspond to the optical path.

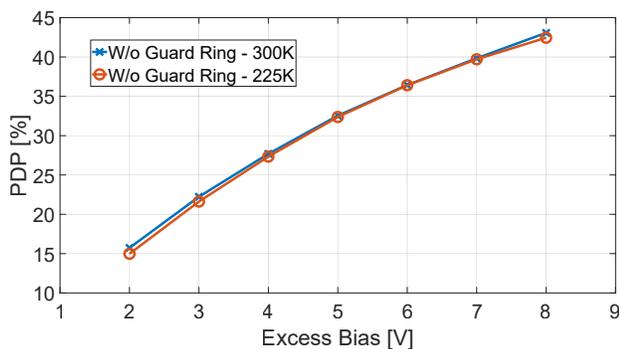


Fig. 12. PDP measurement results of the front-illuminated device without GR at 225K and 300K (1550 nm).

### E. Timing Jitter

Timing jitter is a critical performance metric that impacts the depth accuracy for LiDAR applications. The setup depicted in Fig. 11 was also used for jitter measurement with slight modifications. A reference signal to mark photon arrival is connected to the oscilloscope. Then a histogram of the time differences between the avalanche pulse and the reference signal is produced by the oscilloscope. Measurements were performed at room temperature, 1550 nm wavelength, in single-photon regime. Jitter results are 154 ps and 116 ps at FWHM at 5 and 7 V excess bias as depicted in Fig. 13. Calculated FWHM values include the effect of the laser pulse width. The actual timing jitter of the device is obtained as 149 ps and 109 ps after deconvolution with 40 ps of optical pulse. Figure 13 also shows the jitter result at 5 V excess bias and the Gaussian fit with a standard deviation of 65 ps. Measured diffusion tails for 5 and 7 V excess bias are 110 ps and 92 ps respectively. Compared to the result reported in [11], the diffusion tail observed from the device in this work is longer. This is probably because of the thicker InGaAs absorber region utilized in this work. Thicker InGaAs region results in larger ambiguity in the transit times of the photo-generated carriers from absorber region to multiplication region. It is worth mentioning that jitter measurements using a focused beam instead of wide-area illumination can cause a better estimation of the jitter due to eliminated lateral diffusion as reported here [13]. On the other hand, employing a good sensing circuit with a low threshold and reduced parasitic capacitance may enhance jitter performance [31], [32].

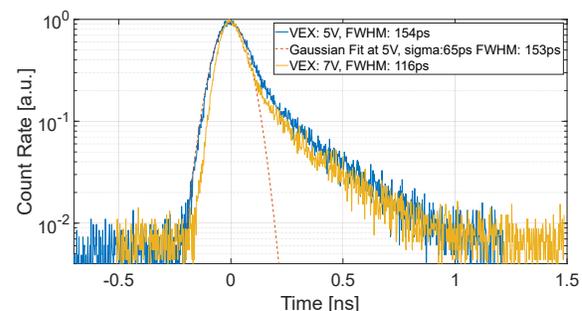


Fig. 13. Jitter measurement results at 5 V and 7 V excess bias. Measurements were done with a focused 1550 nm picosecond pulsed laser at 300K.

## IV. COMPARISON WITH THE STATE-OF-THE-ART

Figure 14 and Table I shows the comparison of DCR per unit area and PDP of our work with state-of-the-art devices. DCR per unit area is preferred as comparison metric of noise since DCR is proportional to device area. The highest PDP was achieved at the lowest DCR per unit area at 225K. This temperature can be reached with a peltier cooling and a hermetic package. Performance comparison at room temperature is also investigated due to interest in LiDAR applications. At this temperature, the devices reported here reach a similar performance as [12] in terms of noise. The importance of active area uniformity and its impact on the noise are discussed in sections B and C by comparing the devices with and without GR. Device designs that utilize double diffusion usually show

TABLE I  
SUMMARY AND COMPARISON OF SPAD PERFORMANCE

Reference	Temperature [K]	Active Diam. [ $\mu$ ]	PDP [%] @ 1550 [nm]	DCR / area [cps / $\mu\text{m}^2$ ] @ PDP [%]	DCR [cps] @ PDP [%]	Jitter [ps] @ PDP [%]
This Work	300	70	15 - 43	36.7 - 1 k @15 - 43	141 k - 4 M @15 - 43	149 - 109 @32 - 43
	225	70	15 - 43	0.4 - 14.4 @15 - 43	1.6 k - 55 k @15 - 43	N.A.
Itzler <i>et al.</i> [4]	225	10	10 - 25	2 - 19 @10 - 25	160 - 1.5 k @10 - 25	N.A.
	225	25	10 - 25	1.8 - 12 @10 - 25	900 - 5.8 k @10 - 25	N.A.
Baba <i>et al.</i> [6]	242	12	10	2.1 k @10	234 k @10	260 <sup>a</sup>
Signorelli <i>et al.</i> [11]	225	10	11 - 30	7 - 71.5 @11 - 30	560 - 1.4 k @11 - 30	225 - 84 @11 - 30
	225	25	11 - 30	2.98 - 13.2 @11 - 30	1460 - 6.5 k @11 - 30	340 - 119 @11 - 30
Fang <i>et al.</i> [12]	303	25	7 - 60	55.9 - 2.5 k @7 - 60	27 k - 1.24 M @7 - 60	N.A.
	233	25	7 - 37	0.5 - 5.5 @7 - 37	260 - 2.5 k @7 - 37	N.A.
Baek <i>et al.</i> [33]	293	25	11 - 27	31 - 100 @11 - 27	15 k - 50 k <sup>b</sup> @11 - 27	N.A.
	233	25	11 - 27	0.8 - 2.8 @11 - 27	370 - 1.4 k <sup>b</sup> @11 - 27	N.A.

<sup>a</sup>Performed at @ 1.6 V<sub>EX</sub>. <sup>b</sup>Calculated from dark count probability and 2 ns pulse width.

higher response around the edge until excess bias reaches 5 V [13], [19], [34]. One of the remarkable features of SAG-based InGaAs/InP SPAD is that, with only one-step Zn-diffusion, avalanche generation is well confined at the device center even at 3 V excess bias. Reducing these edge effects is likely the reason such a low DCR per unit area is achieved. Thanks to the minimized contribution of the edges to DCR, a very small change in our DCR per unit area is expected while shrinking the device size as DCR should scale linearly with the device area.

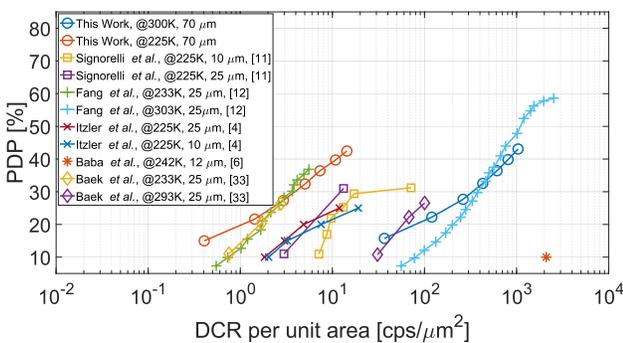


Fig. 14. Comparison of DCR and PDP to state-of-the-art.

## V. CONCLUSION

In this work, a novel InGaAs/InP structure is reported. SAG-based diffusion approach achieves a uniform electric field in the avalanche region with a single diffusion step. Devices reported here show one of the highest efficiencies in SWIR with minimal noise. The pixel photoresponse is also very uniform, and does not show significant edge field enhancement. A GR-free structure would provide a path toward a higher pixel fill factor for future high-density arrays. Furthermore, it can operate at room temperature. All these results indicate that SAG-based SPAD is one of the best candidates for a LiDAR camera thanks to their reproducibility and scalability to large arrays. In future work, pixel sizes will be scaled down while Zn diffusion and SAG thickness will be optimized for the best performance, and SPAD arrays will be fabricated with minimum pixel pitch to be utilized in LiDAR applications.

## ACKNOWLEDGMENT

This work was supported by the High Throughput and Secure Networks Challenge Program at the National Research Council of Canada.

## REFERENCES

- [1] R. H. Hadfield, "Single-photon detectors for optical quantum information applications," *Nature Photonics*, vol. 3, no. 12, pp. 696–705, Dec. 2009.
- [2] P. Eraerds, M. Legr, J. Zhang, H. Zbinden, and N. Gisin, "Photon counting OTDR: Advantages and limitations," *J. Lightwave Technol.*, vol. 28, no. 6, pp. 952–964, Mar. 2010.
- [3] X. Jiang, S. R. Wilton, I. Kudryashov, M. A. Itzler, M. Entwistle, J. Kotelnikov, A. Katsnelson, B. Piccione, M. Owens, K. Slomkowski, S. Roszko, and S. Rangwala, "InGaAsP/InP Geiger-mode APD-based LiDAR," in *Optical Sensing, Imaging, and Photon Counting: From X-Rays to THz*, vol. 10729, Sep. 2018.
- [4] M. A. Itzler, M. Entwistle, U. Krishnamachari, M. Owens, X. Jiang, K. Slomkowski, and S. Rangwala, "SWIR Geiger-mode APD detectors and cameras for 3D imaging," in *Advanced Photon Counting Techniques VIII*, Jun. 2014, p. 37–48.
- [5] C. Yu, M. Shangguan, H. Xia, J. Zhang, X. Dou, and J. W. Pan, "Fully integrated free-running InGaAs/InP single-photon detector for accurate lidar applications," *Opt. Express*, vol. 25, no. 13, pp. 14611–14620, Jun. 2017.
- [6] T. Baba, Y. Suzuki, K. Makino, T. Fujita, T. Hashi, S. Adachi, S. Nakamura, and K. Yamamoto, "Development of an InGaAs SPAD 2D array for flash LIDAR," in *Quantum Sensing and Nano Electronics and Photonics XV*, vol. 10540, Jan. 2018.
- [7] F. Marsili, V. B. Verma, J. A. Stern, S. Harrington, A. E. Lita, T. Gerrits, I. Vayshenker, B. Baek, M. D. Shaw, R. P. Mirin, and S. W. Nam, "Detecting single infrared photons with 93% system efficiency," *Nature Photonics*, vol. 7, no. 3, pp. 210–214, Mar. 2013.
- [8] W. J. Zhang, L. X. You, H. Li, J. Huang, C. L. Lv, L. Zhang, X. Y. Liu, J. J. Wu, Z. Wang, and X. M. Xie, "NbN superconducting nanowire single photon detector with efficiency over 90% at 1550 nm wavelength operational at compact cryocooler temperature," *Science China Physics, Mechanics & Astronomy*, vol. 60, no. 12, pp. 1869–1927, Oct. 2017.
- [9] S. Miki, T. Yamashita, H. Terai, and Z. Wang, "High performance fiber-coupled NbTiN superconducting nanowire single photon detectors with Gifford-McMahon cryocooler," *Opt. Express*, vol. 21, no. 8, pp. 10208–10214, Apr. 2013.
- [10] P. Vines, K. Kuzmenko, D. C. S. Dumas, M. M. Mirza, R. W. Millar, D. J. Paul, and G. S. Buller, "High performance planar germanium-on-silicon single-photon avalanche diode detectors," *Nature Communications*, vol. 10, no. 1, Mar. 2019.
- [11] F. Signorelli, F. Telesca, E. Conca, A. D. Frera, A. Ruggeri, A. Giudice, and A. Tosi, "Low-noise InGaAs/InP single-photon avalanche diodes for fiber-based and free-space applications," *IEEE Journal of Selected Topics in Quantum Electronics*, vol. 28, no. 2, pp. 1–10, Mar. 2022.

[12] Y. Q. Fang, W. Chen, T. H. Ao, C. Liu, L. Wang, X. J. Gao, J. Zhang, and J. W. Pan, "InGaAs/InP single-photon detectors with 60% detection efficiency at 1550 nm," *Review of Scientific Instruments*, vol. 91, no. 8, p. 083102, 2020.

[13] A. Tosi, N. Calandri, M. Sanzaro, and F. Acerbi, "Low-noise, low-jitter, high detection efficiency InGaAs/InP single-photon avalanche diode," *IEEE Journal of Selected Topics in Quantum Electronics*, vol. 20, no. 6, pp. 192–197, Nov. 2014.

[14] J. Zhang, M. A. Itzler, H. Zbinden, and J.-W. Pan, "Advances in InGaAs/InP single-photon detector systems for quantum communication," *Light: Science & Applications*, vol. 4, no. 5, p. e286, May 2015.

[15] K. Lee and K. Yang, "Analysis of InGaAs/InP Single-Photon Avalanche Diodes With the Multiplication Width Variation," *IEEE Photonics Technology Letters*, vol. 26, no. 10, pp. 999–1002, Mar. 2014.

[16] K. Lee, "Analysis of InP-based single photon avalanche diodes based on a single recess-etching process," *Japanese Journal of Applied Physics*, vol. 57, no. 4, p. 042203, Mar. 2018.

[17] O. Pitts, M. Hisko, W. Benyon, G. Bonneville, C. Storey, and A. SpringThorpe, "Planar avalanche photodiodes with edge breakdown suppression using a novel selective area growth based process," *Journal of Crystal Growth*, vol. 470, pp. 149–153, Jul. 2017.

[18] S. Forrest, R. Smith, and O. Kim, "Performance of In<sub>0.53</sub>Ga<sub>0.47</sub>As/InP avalanche photodiodes," *IEEE Journal of Quantum Electronics*, vol. 18, no. 12, pp. 2040–2048, Dec. 1982.

[19] M. A. Itzler, X. Jiang, M. Entwistle, K. Slomkowski, A. Tosi, F. Acerbi, F. Zappa, and S. Cova, "Advances in InGaAsP-based avalanche diode single photon detectors," *Journal of Modern Optics*, vol. 58, no. 3-4, pp. 174–200, Jan. 2011.

[20] M. Gibbon, J. P. Stagg, C. G. Cureton, E. J. Thrush, C. J. Jones, R. E. Mallard, R. E. Pritchard, N. Collis, and A. Chew, "Selective-area low-pressure MOCVD of GaInAsP and related materials on planar InP substrates," *IOP Publishing*, vol. 8, no. 6, pp. 998–1010, Jun. 1993.

[21] O. Pitts, M. Hisko, W. Benyon, S. Raymond, and A. SpringThorpe, "Optimization of MOCVD-diffused p-InP for planar avalanche photodiodes," *Journal of Crystal Growth*, vol. 393, pp. 85–88, May 2014.

[22] J. Donnelly, E. Duerr, K. McIntosh, E. Dauler, D. Oakley, S. Groves, C. Vineis, L. Mahoney, K. Molvar, P. Hopman, K. Jensen, G. Smith, S. Verghese, and D. Shaver, "Design considerations for 1.06μm InGaAsP-InP geiger-mode avalanche photodiodes," *IEEE Journal of Quantum Electronics*, vol. 42, no. 8, pp. 797–809, Jul. 2006.

[23] Y. Okuto and C. Crowell, "Threshold energy effect on avalanche breakdown voltage in semiconductor junctions," *Solid-State Electronics*, vol. 18, no. 2, pp. 161–168, Feb. 1975.

[24] R. K. Ahrenkiel, R. Ellingson, S. Johnston, and M. Wanlass, "Recombination lifetime of In<sub>0.53</sub>Ga<sub>0.47</sub>As as a function of doping density," *Applied Physics Letters*, vol. 72, no. 26, pp. 3470–3472, Jun. 1998.

[25] N. M. Schmidt, M. Levinshtein, S. Romyantsev, and M. Shur, *Handbook Series on Semiconductor Parameters*, 1996.

[26] M. Sugiyama, N. Waki, Y. Nobumori, H. Song, T. Nakano, T. Arakawa, Y. Nakano, and Y. Shimogaki, "Control of abnormal edge growth in selective area MOVPE of InP," *Journal of Crystal Growth*, vol. 287, no. 2, pp. 668–672, Jan. 2006.

[27] C. Hu, X. Zheng, J. C. Campbell, B. M. Onat, X. Jiang, and M. A. Itzler, "Characterization of an InGaAs/InP-based single-photon avalanche diode with gated-passive quenching with active reset circuit," *Journal of Modern Optics*, vol. 58, no. 3-4, pp. 201–209, Sep. 2011.

[28] Y. S. Lee, K. Y. Chen, S. Y. Chien, and S. C. Chang, "Characteristics of charge persistence in InGaAs/InP single-photon avalanche diode," *IEEE Photonics Technology Letters*, vol. 30, no. 22, pp. 1980–1982, Oct. 2018.

[29] N. Calandri, M. Sanzaro, A. Tosi, and F. Zappa, "Charge persistence in InGaAs/InP single-photon avalanche diodes," *IEEE Journal of Quantum Electronics*, vol. 52, no. 3, pp. 1–7, Feb. 2016.

[30] Y. Okuto and C. R. Crowell, "Ionization coefficients in semiconductors: A nonlocalized property," *Phys. Rev. B*, vol. 10, no. 10, pp. 4284–4296, Nov. 1974.

[31] F. Acerbi, A. D. Frera, A. Tosi, and F. Zappa, "Fast active quenching circuit for reducing avalanche charge and afterpulsing in InGaAs/InP single-photon avalanche diode," *IEEE Journal of Quantum Electronics*, vol. 49, no. 7, pp. 563–569, Apr. 2013.

[32] F. Gramuglia, M.-L. Wu, C. Bruschini, M.-J. Lee, and E. Charbon, "A low-noise CMOS SPAD pixel with 12.1 ps SPTR and 3 ns dead time," *IEEE J. Sel. Topics Quantum Electron.*, vol. 13, no. X, p. X, Sep. X.

[33] S.-H. Baek, S.-C. Yang, C.-Y. Park, C.-W. Park, S.-B. Cho, and S.-W. Ryu, "Room temperature quantum key distribution characteristics of low-noise InGaAs/InP single-photon avalanche diode," *Journal of the Korean Physical Society*, vol. 78, no. 7, pp. 634–641, Apr. 2021.

[34] A. Tosi, F. Acerbi, A. Dalla Mora, M. A. Itzler, and X. Jiang, "Active area uniformity of InGaAs/InP single-photon avalanche diodes," *IEEE Photonics Journal*, vol. 3, no. 1, pp. 31–41, Dec. 2011.



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